

International **IR** Rectifier

- Logic-Level Gate Drive
- Ultra Low On-Resistance
- Surface Mount (IRLR2905)
- Straight Lead (IRLU2905)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	42 $\text{\textcircled{S}}$	
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	30	A
I_{DM}	Pulsed Drain Current $\text{\textcircled{I}}$	160	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy $\text{\textcircled{D}}$	210	mJ
I_{AR}	Avalanche Current $\text{\textcircled{I}}$	25	A
E_{AR}	Repetitive Avalanche Energy $\text{\textcircled{I}}$	11	mJ
dv/dt	Peak Diode Recovery dv/dt $\text{\textcircled{S}}$	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	$^\circ\text{C}$

Thermal Resistance

	Parameter	Typ.	Max.	Units
R_{0JC}	Junction-to-Case	—	1.4	
R_{0JA}	Case-to-Ambient(PCB mount)**	—	50	$^\circ\text{C/W}$
R_{0JA}	Junction-to-Ambient	—	110	

** When mounted on 1" square PCB (FR-4 or G-10 Material) .

For recommended footprint and soldering techniques refer to application note #AN-994

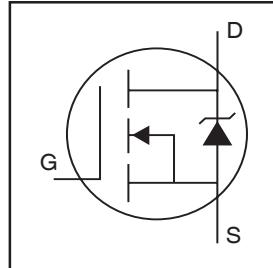
www.irf.com

1

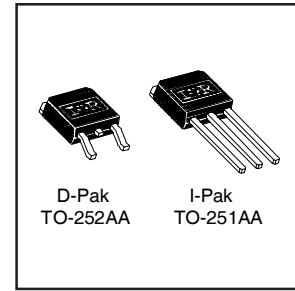
12/7/04

PD- 95084A
IRLR/U2905PbF

HEXFET® Power MOSFET

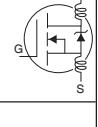


$V_{DSS} = 55\text{V}$
$R_{DS(on)} = 0.027\Omega$
$I_D = 42\text{A} \text{\textcircled{S}}$

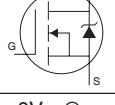


D-Pak TO-252AA I-Pak TO-251AA

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}/\Delta T_J}$	Breakdown Voltage Temp. Coefficient	—	0.070	—	$\text{V}/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{\text{DS}(\text{on})}$	Static Drain-to-Source On-Resistance	—	—	0.027	W	$V_{\text{GS}} = 10\text{V}, I_D = 25\text{A}$ ④
		—	—	0.030		$V_{\text{GS}} = 5.0\text{V}, I_D = 25\text{A}$ ④
		—	—	0.040		$V_{\text{GS}} = 4.0\text{V}, I_D = 21\text{A}$ ④
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$
g_{fs}	Forward Transconductance	21	—	—	S	$V_{\text{DS}} = 25\text{V}, I_D = 25\text{A}$ ⑦
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{\text{DS}} = 55\text{V}, V_{\text{GS}} = 0\text{V}$
		—	—	250		$V_{\text{DS}} = 44\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{\text{GS}} = 16\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{\text{GS}} = -16\text{V}$
Q_g	Total Gate Charge	—	—	48	nC	$I_D = 25\text{A}$
Q_{gs}	Gate-to-Source Charge	—	—	8.6		$V_{\text{DS}} = 44\text{V}$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	25		$V_{\text{GS}} = 5.0\text{V}, \text{See Fig. 6 and 13}$ ④⑦
$t_{\text{d}(\text{on})}$	Turn-On Delay Time	—	11	—	ns	$V_{\text{DD}} = 28\text{V}$
t_r	Rise Time	—	84	—		$I_D = 25\text{A}$
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time	—	26	—		$R_G = 3.4\Omega, V_{\text{GS}} = 5.0\text{V}$
t_f	Fall Time	—	15	—		$R_D = 1.1\Omega, \text{See Fig. 10}$ ④⑦
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑥
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1700	—		$V_{\text{GS}} = 0\text{V}$
C_{oss}	Output Capacitance	—	400	—	pF	$V_{\text{DS}} = 25\text{V}$
C_{rss}	Reverse Transfer Capacitance	—	150	—		$f = 1.0\text{MHz}, \text{See Fig. 5}$ ⑦

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	42 ⑤	A	MOSFET symbol showing the integral reverse p-n junction diode.
	Pulsed Source Current (Body Diode) ①	—	—	160		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 25\text{A}, V_{\text{GS}} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	80	120	ns	$T_J = 25^\circ\text{C}, I_F = 25\text{A}$
Q_{rr}	Reverse Recovery Charge	—	210	320	nC	$dI/dt = 100\text{A}/\mu\text{s}$ ④⑦
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{\text{DD}} = 25\text{V}$, starting $T_J = 25^\circ\text{C}$, $L = 470\mu\text{H}$, $R_G = 25\Omega$, $I_{AS} = 25\text{A}$. (See Figure 12)
- ③ $I_{SD} \leq 25\text{A}$, $dI/dt \leq 270\text{A}/\mu\text{s}$, $V_{\text{DD}} \leq V_{(\text{BR})\text{DSS}}$, $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

- ⑤ Calculated continuous current based on maximum allowable junction temperature; Package limitation current = 20A.
- ⑥ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact.
- ⑦ Uses IRLZ44N data and test conditions.

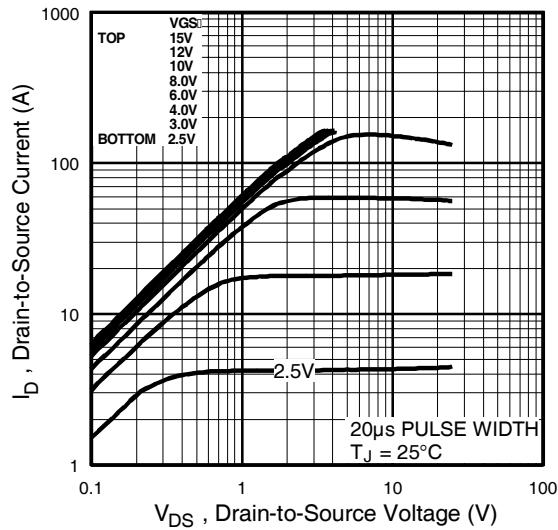


Fig 1. Typical Output Characteristics

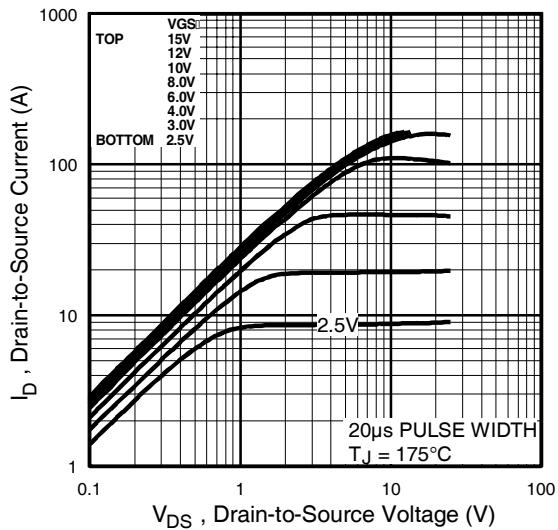


Fig 2. Typical Output Characteristics

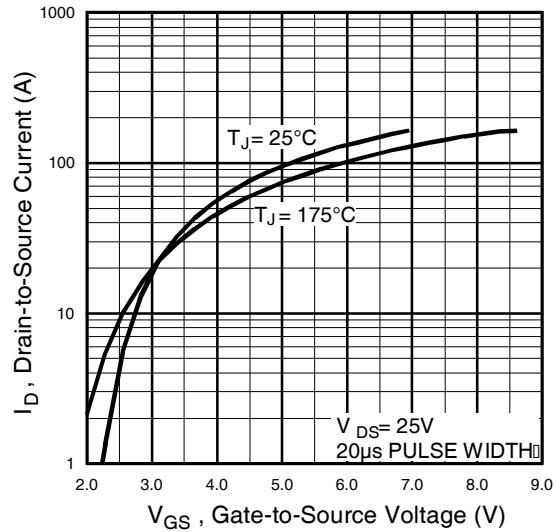


Fig 3. Typical Transfer Characteristics

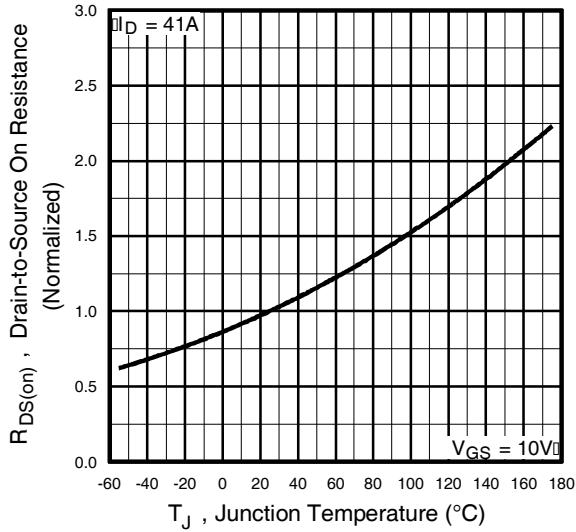


Fig 4. Normalized On-Resistance
Vs. Temperature

IRLR/U2905PbF

International
IR Rectifier

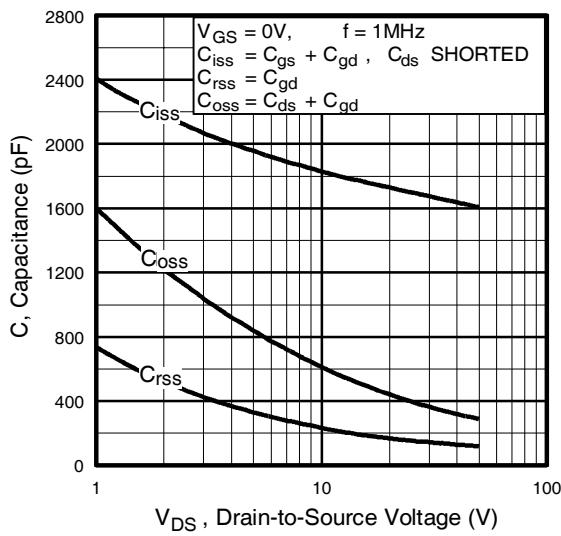


Fig 5. Typical Capacitance Vs.
Drain-to-Source Voltage

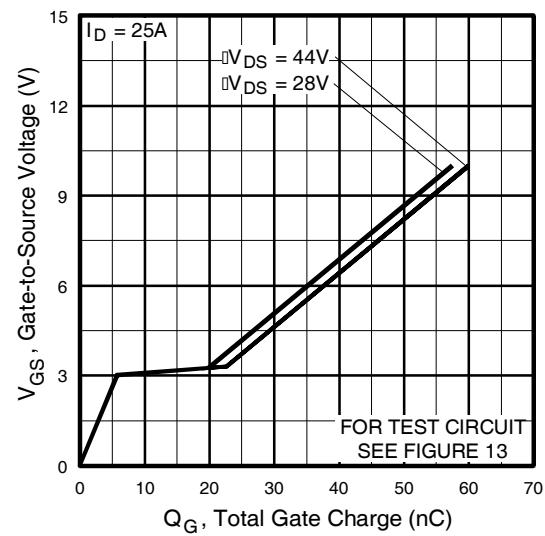


Fig 6. Typical Gate Charge Vs.
Gate-to-Source Voltage

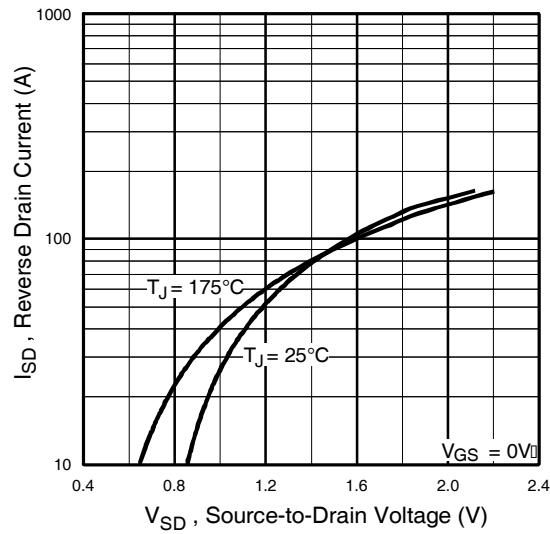


Fig 7. Typical Source-Drain Diode
Forward Voltage

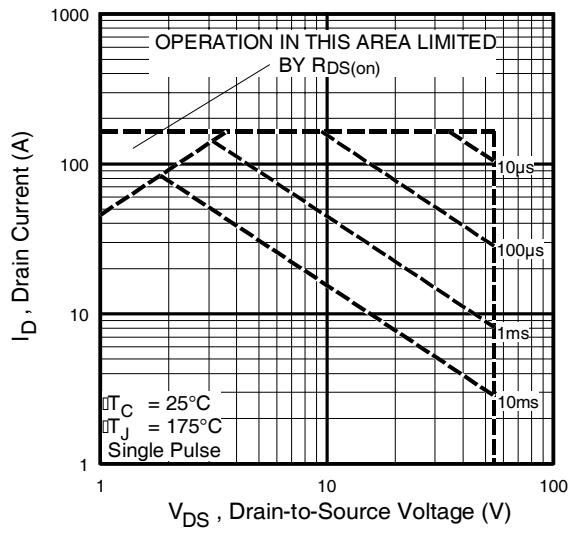


Fig 8. Maximum Safe Operating Area

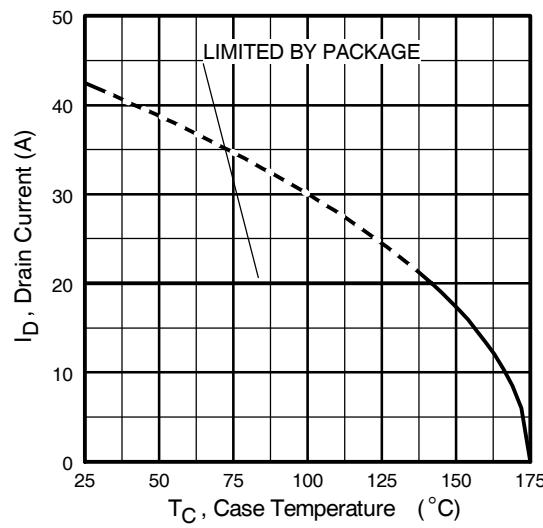


Fig 9. Maximum Drain Current Vs.
Case Temperature

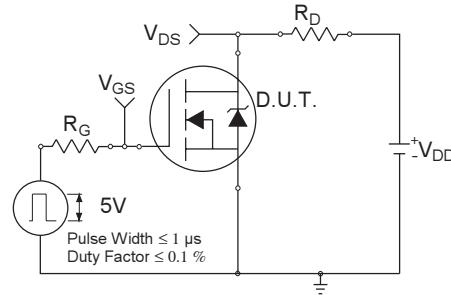


Fig 10a. Switching Time Test Circuit

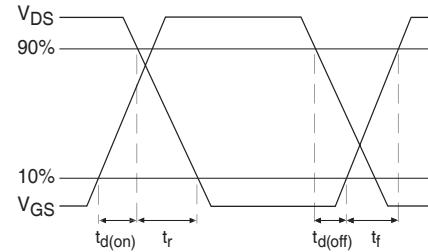


Fig 10b. Switching Time Waveforms

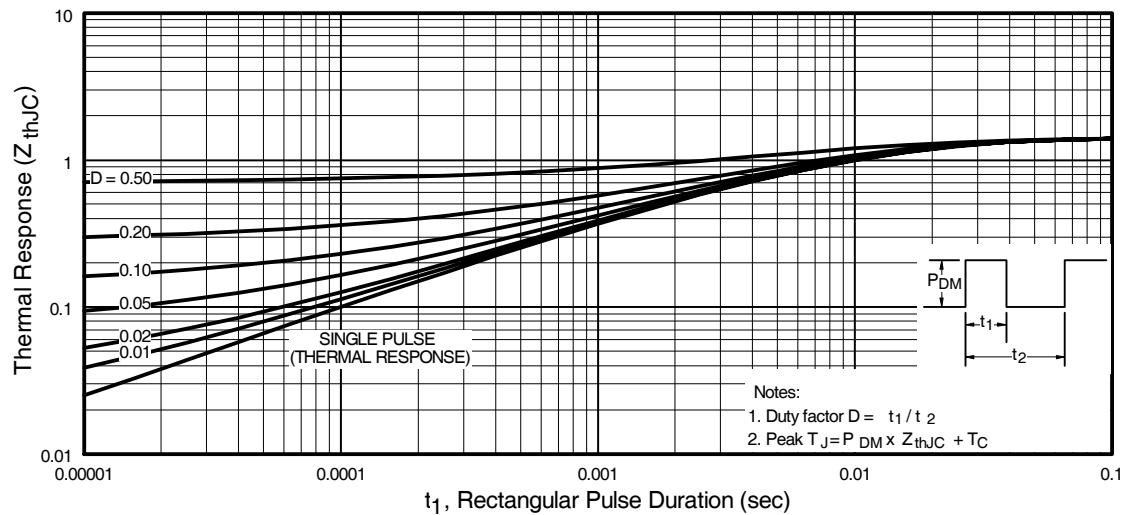


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRLR/U2905PbF

International
IR Rectifier

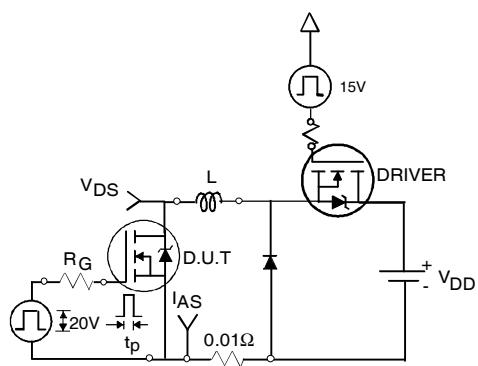


Fig 12a. Unclamped Inductive Test Circuit

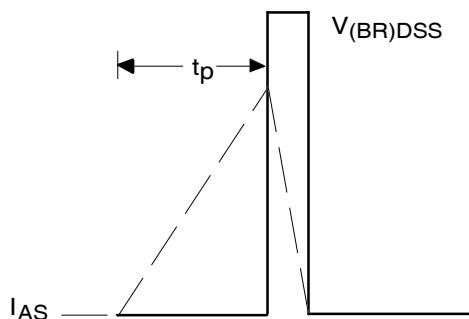


Fig 12b. Unclamped Inductive Waveforms

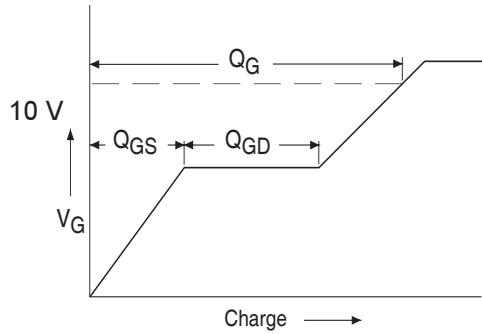


Fig 13a. Basic Gate Charge Waveform

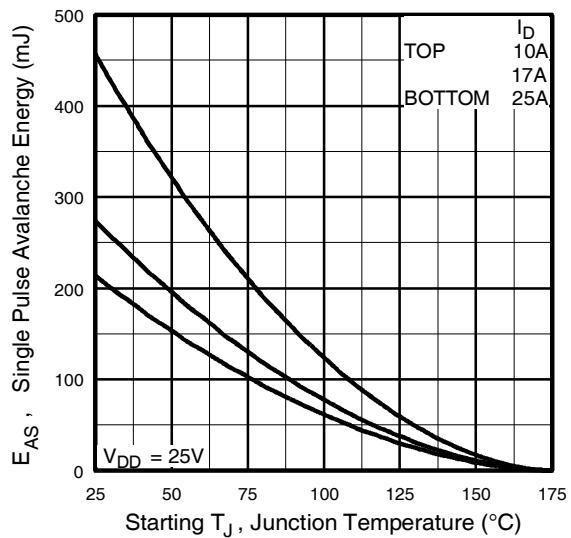


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

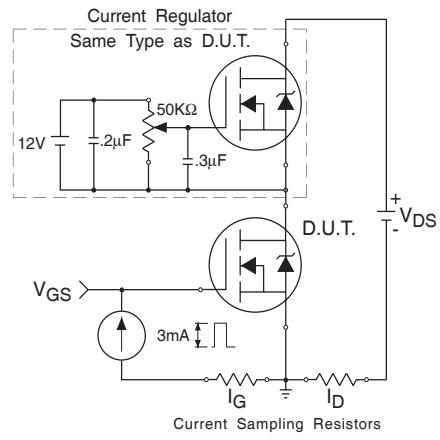
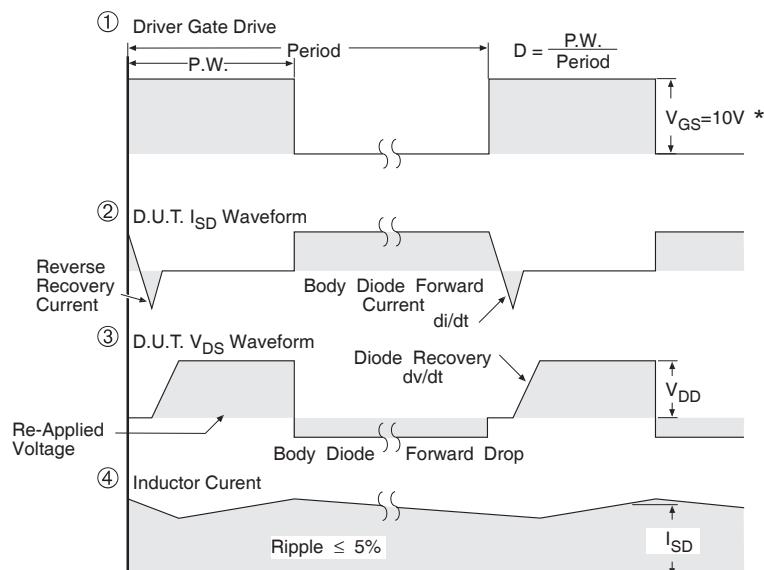
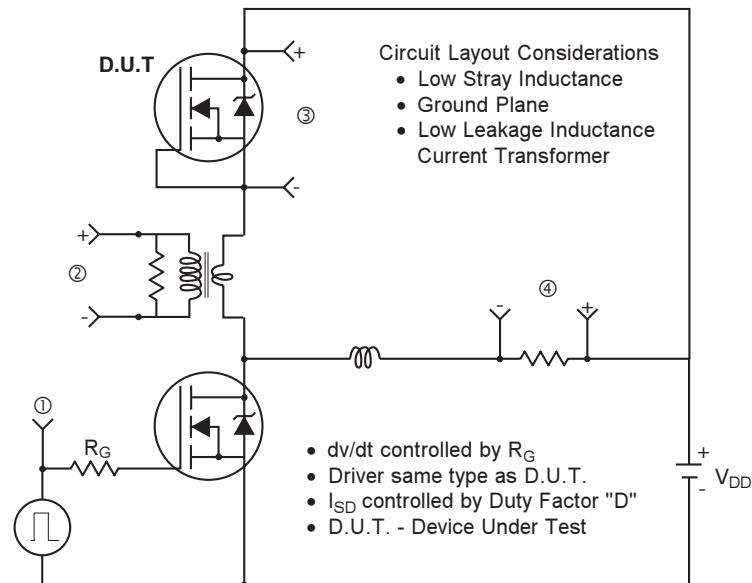


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

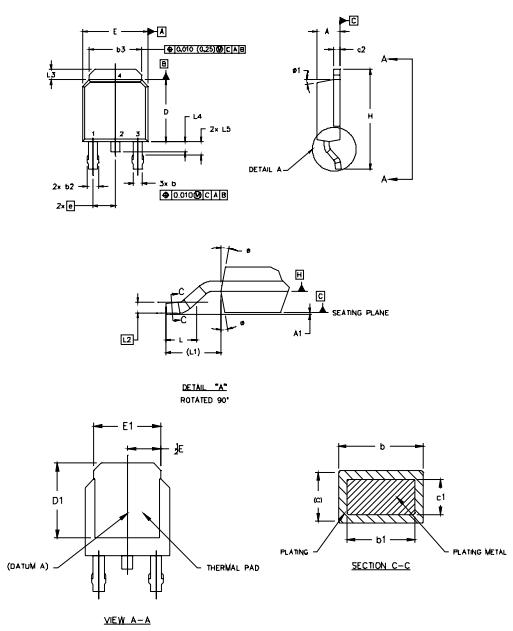
Fig 14. For N-Channel HEXFETs

IRLR/U2905PbF

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)

International
IR Rectifier



NOTES:

- 1.0 DIMINISHING AND TAPERING PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3.0 DEAD DIMENSION UNCONTROLLED IN INCHES.
- 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .006 [0.152] INCHES.
- 6.0 DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.127] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS			NOTES
	MILLIMETERS	INCHES	MAX.	
A	2.16	.085	.084	
A1	.015	.006	.005	
B	.644	.025	.038	5
B1	.51	.020	.045	
B2	.496	.019	.275	
C	.46	.018	.024	5
C1	.041	.0016	.002	6
C2	.046	.0018	.038	5
D	.51	.020	.245	6
D1	.571	.022	.205	4
E	.629	.025	.265	6
E1	-	.170	-	4
F	2.22	.087	.086	
H	.845	.0331	.010	
L	1.40	.055	.070	
L1	2.74	.108	.108	
L2	0.001 BSC	.000 BSC		
L3	.080	.003	.050	
L4	.100	.004	.040	
L5	.114	.0045	.060	
M	.07	.003	.010	
N	.07	.003	.015	

LEAD ASSIGNMENTS

HEXFET

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE
- 4 - DRAIN

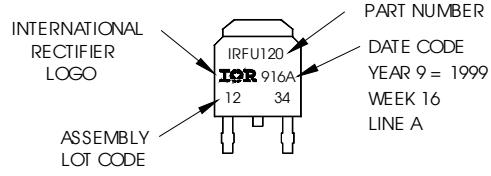
IGBTs, CoPACK

- 1 - GATE
- 2 - COLLECTOR
- 3 - Emitter
- 4 - COLLECTOR

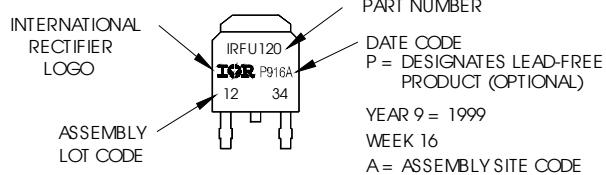
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

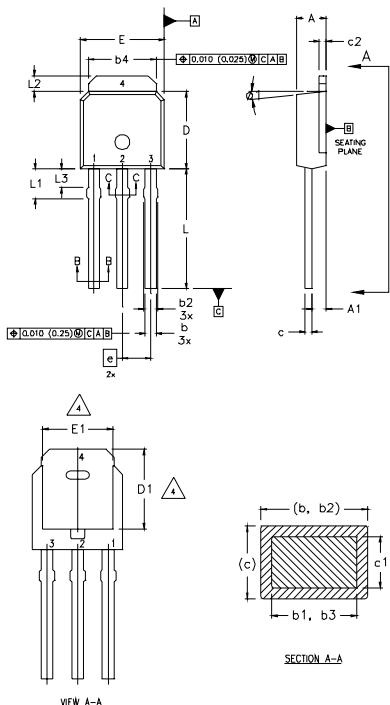


OR



I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
5. LEAD DIMENSION UNCONTROLLED IN L3.
6. DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
7. OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
8. CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	0.46	0.66	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.36	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	
L3	1.14	1.52	0.045	0.060	
g1	0"	15'	0"	15"	5

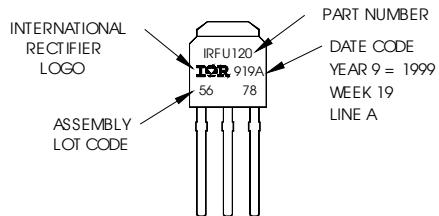
LEAD ASSIGNMENTS

HEXFET
1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

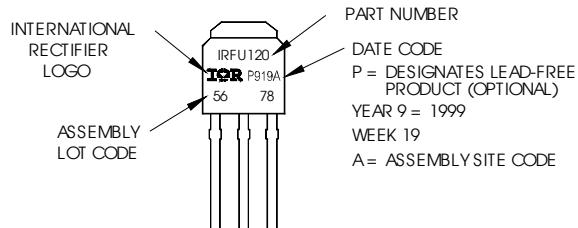
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
 WITH ASSEMBLY
 LOT CODE 5678
 ASSEMBLED ON WW19, 1999
 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"

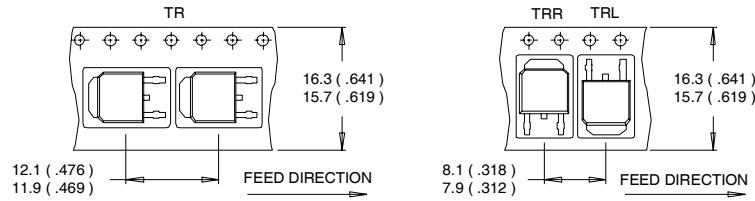


OR



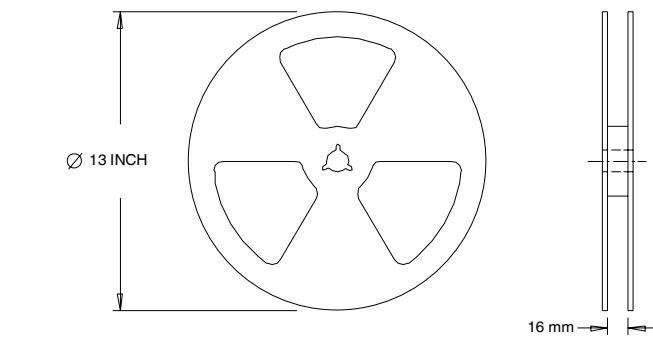
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.
Data and specifications subject to change without notice. 12/04

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>